

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning at page 37, line 7, with the following rewritten paragraph:

--With an organic semiconductor, although the mechanism of channel formation is still not yet clarified, it is known that the channel width may reach ~~10,000 nm~~ 100 nm, being thicker than the typical thickness (~~5,000 nm~~ 50 nm) of the source/drain electrode of a TFT device. Even if the channel width is ~~10,000 nm~~ 100 nm, in the active device 20 shown in FIG. 1, wherein the thickness of the source/drain electrode is formed to be ~~4,000 nm~~ 40 nm, and the semiconductor layer is formed to be ~~10,000 nm~~ 100 nm, because a TFT device having a channel length of ~~6,000 nm~~ 60 nm is obtained, and the channel is formed all over the semiconductor layer, it becomes possible to modulate the source-drain current by applying a gate voltage.--